



SHEET 1 OF 1

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 243579US0X		SERIAL NO. 10/677,309	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Tetsuo SUZUKI, et al.			
				FILING DATE October 3, 2003		GROUP	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>MJP</i>	AA	6,451,696	09/17/2002	Y. HARA, et al.			
<i>MJP</i>	AB	6,406,923	06/18/2002	H. INOUE, et al.			
<i>MJP</i>	AC	6,384,415	05/07/2002	T. SUZUKI, et al.			
<i>MJP</i>	AD	5,885,334	03/23/1999	T. SUZUKI, et al.			
<i>MJP</i>	AE	5,855,735	01/05/1999	S. TAKADA, et al.			
<i>MJP</i>	AF	5,622,875	04/22/1997	J. E. LAWRENCE			
<i>MJP</i>	AG	3,923,567	12/02/1975	J. E. LAWRENCE			
	AH						
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO		
<i>MJP</i>	AI	2002-270568	09/20/2002	JAPAN (with English Abstract)			X
<i>MJP</i>	AJ	2002-158207	05/31/2002	JAPAN (with English Abstract)			X
<i>MJP</i>	AK	2001-213694	08/07/2001	JAPAN (with English Abstract)			X
<i>MJP</i>	AL	2001-174375	06/29/2001	JAPAN (with English Abstract)			X
<i>MJP</i>	AM	2000-164558	06/16/2000	JAPAN (with English Abstract)			X
<i>MJP</i>	AN	9-064133	03/07/1997	JAPAN (with English Abstract)			X
<i>MJP</i>	AO	9-017833	01/17/1997	JAPAN (with English Abstract)			X
<i>MJP</i>	AP	7-122532	05/12/1995	JAPAN (with English Abstract)			X
<i>MJP</i>	AQ	6-168998	06/14/1994	JAPAN (with English Abstract)			X
<i>MJP</i>	AR	5-315428	11/26/1993	JAPAN (with English Abstract)			X
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OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
<i>MJP</i>	AT	E. R. WEBER, Applied Physics A, vol. 30, pages 1-22, "TRANSITION METALS IN SILICON", 1983					
<i>MJP</i>	AU	H. PRIGGE, et al., J. Electrochem. Soc., Technical Papers, Solid-State Science and Technology, vol. 138, no. 5, pages 1385-1389, "ACCEPTOR COMPENSATION IN SILICON INDUCED BY CHEMOMECHANICAL POLISHING", May 1991					
<i>MJP</i>	AV	M. B. SHABANI, et al., J. Electrochem. Soc., vol. 143, no. 6, pages 2025-2029, "LOW-TEMPERATURE OUT-DIFFUSION OF Cu FROM SILICON WAFERS", June 1996					
<i>MJP</i>	AW	A. A. ISTRATOV, et al., Physical Review Letters, vol. 81, no. 6, pages 1243-1246, "INTRINSIC DIFFUSION COEFFICIENT OF INTERSTITIAL COPPER IN SILICON", August 10, 1998					
<i>MJP</i>	AX	C. BEAUDRY, et al., MICRO, pages 41-54, "EVALUATING WAFER RECLAIM TECHNIQUES IN EMERGING COPPER PROCESSES", March 2000					
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Examiner <i>Muneen J. Francis</i>					Date Considered 12/9/2005		
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							